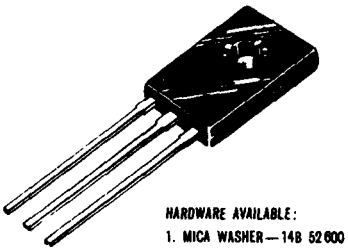
BD562

PNP SILICON MEDIUM-POWER TRANSISTOR

- Designed for 5 to 10W Audio Amplifiers
- BD562 is complementary to BD561
- P_D of 40W with T_j of 150° C
- Case 77 package is Pin compatible with SOT-9

4 AMPERE
POWER TRANSISTOR
PNP SILICON
40 VOLTS
40 WATTS



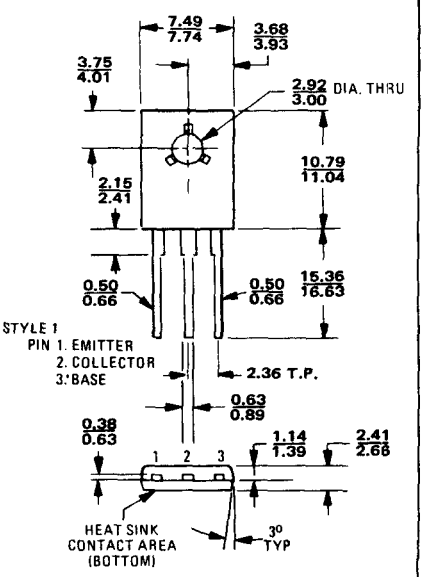
HARDWARE AVAILABLE:
1. MICA WASHER—14B 52 600 F03
2. LOCK WASHER—04A 52 200 F01

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	45	Vdc
Emitter-Base Voltage	V_{EBO}	5	Vdc
Collector Current	I_C	4	Adc
Base Current	I_B	2	Adc
Total Device Dissipation $T_C = 25°$ C	P_D	40	Watts
Derate above 25° C		320	mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	—65 to +150	° C

THERMAL CHARACTERISTICS

	Symbol	Max.	Unit
Thermal Resistance, Junction to Case	θ_{JC}	3.12	° C/W



When mounting the device, torque not to exceed 0.07 m-kg.

If lead bending is required, use suitable clamps or other supports between transistor case and point of bend.
All dimensions in millimeters

CASE 77-03

ELECTRICAL CHARACTERISTICS (T_C = 25° C unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
Collector-Emitter Sustaining Voltage (I_C = 0.1 Adc, I_B = 0)	$V_{CEO(sus)}$	40	—	Vdc
Collector Cutoff Current (V_{CB} = 45 V, I_E = 0)	I_{CBO}	—	0.1	mAdc
Emitter Cutoff Current (V_{BE} = 5.0 V, I_C = 0)	I_{EBO}	—	0.1	mAdc
DC Current Gain (I_C = 50 mA V_{CE} = 1.0 V) * (I_C = 500 mA V_{CE} = 1.0 V) * (I_C = 2.0 A V_{CE} = 1.0 V) *	h_{FE}	 40 60 40	— — — —	—
Collector-Emitter Saturation Voltage (I_C = 1.0 A I_B = 0.1 A) *	$V_{CE(sat)}$	—	0.5	Vdc
Base-Emitter On Voltage (I_C = 2.0 A V_{CE} = 1.0 V) *	$V_{BE(on)}$	—	1.2	Vdc

* Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0 %